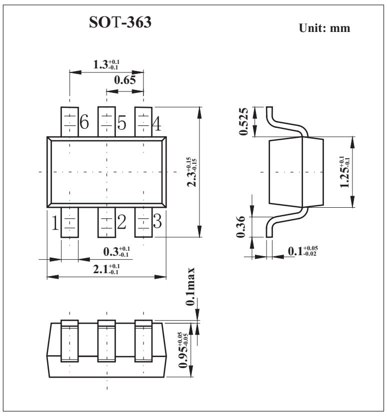
Schottky Barrier Diodes

1PS88SB48



Features

- Ultra fast switching speed
- Low forward voltage
- Small SMD package
- Guard ring protected
- Absorbs very high surge pulse
- Low capacitance.

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Conditions	Min	Max	Unit
continuous reverse voltage	V_R			40	V
continuous forward current	I_F			120	mA
repetitive peak forward current	I_{FRM}	$t_p \leqslant 1$ s; $\delta \leqslant 0.5$		120	mA
non-repetitive peak forward current	I_{FSM}	$t_p < 10$ ms		200	mA
storage temperature	T_{stg}		-65	+150	℃
junction temperature	T_j			150	℃
operating ambient temperature	T_{amb}		-65	+150	℃
thermal resistance from junction to ambient	$R_{th\ j\text{-}a}$			416	K/W

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Max	Unit
continuous forward voltage	V_F	I_F = 1 mA	380	mV
		I_F = 10 mA	500	mV
		I_F = 40 mA	1	V
continuous reverse current	I_R	V_R = 30 V	1	μA
		V_R = 80 V	10	
diode capacitance	C_T	V_R=0 V,f=1 MHz	5	pF

Note

1. Pulse test: tp = 300 μs; δ = 0.02.

Marking

Marking	8t5